

CLAIM AMENDMENTS

Claims 1-6 (Cancelled).

7. (Currently Amended) A semiconductor laser device fabricating method including ~~the steps of~~:

~~firstly forming a first-clad cladding layer of a first conductivity type, an active layer of having a quantum well structure, and a first-second-clad second cladding layer of a second conductivity type successively on a semiconductor substrate of the first conductivity type;~~

~~secondly forming on a surface of the first-second-clad second cladding layer a mask pattern for impurity implantation having an opening in a region where a resonator facet of a semiconductor laser device is expected to be formed;~~

~~thirdly disordering the active layer near the resonator facet by introducing impurities with using the mask pattern for introducing impurity used as a mask;~~

~~fourthly applying pumped pump light to the disordered region to generate photo luminescence photoluminescence therefrom, and measuring a wavelength of the photo luminescence as a basis photoluminescence for predicting a level of COD catastrophic optical damage (COD) degradation;~~

~~fifthly forming a second-second-clad second cladding layer of the second conductivity type on the surface of said first-second-clad second cladding layer, after removing the mask pattern;~~

~~sixthly forming on a surface of the said second-second-clad second cladding layer a stripe-shaped mask pattern in a manner, opposed to the disordered active layer, across the first and the second-second-clad layer second cladding layers, the stripe-shaped mask pattern extending in a resonator lengthwise direction; and~~

~~seventhly forming an optical waveguide including the second-second-clad second cladding layer with the stripe-shaped mask pattern used as a mask.~~

8. (Currently Amended) ~~A~~The semiconductor laser device fabricating method according to claim 7, wherein, if the semiconductor laser device ~~has an oscillation produces light having a wavelength in the range of 770 to 810 nm, if λ_{dpl} is assumed to denote denotes, in nm, the wavelength of photo luminescence photoluminescence generated by application of pumped pump light to the disordered region, and if λ_{apl} to represent represents, in nm, the wavelength of photo luminescence photoluminescence generated by application of pumped pump light to the active layer, and if a blue shift~~

amount λ_{bl} , in nm, is ~~defined as~~ equal to $\lambda_{apl} - \lambda_{dpl}$, then ~~the blue shift amount λ_{bl} meets a condition of $\lambda_{bl} \leq 20$ when said fourth step the pump light is carried out applied to the disordered region.~~

9. (Currently Amended) ~~A~~The semiconductor laser device fabricating method according to claim 8, wherein, if P_{cod} ~~is assumed to denote~~ denotes, in mW, the COD level of the laser device, ~~then the blue shift amount λ_{bl} in nm further meets a condition of~~ $(P_{cod} - 85)/5.6 \leq \lambda_{bl} \leq (P_{cod} - 135.0)/1.3$.